Michelle Y Simmons

List of Publications by Year
in descending order

349 papers	11,423 citations	38742 50 h-index	39675 94 g-index
354 all docs	354 docs citations	354 times ranked	5938 citing authors

#	Article	IF	Citations
1	Spin-Photon Coupling for Atomic Qubit Devices in Silicon. Physical Review Applied, 2022, 17, .	3.8	6
2	Engineering topological states in atom-based semiconductor quantum dots. Nature, 2022, 606, 694-699.	27.8	48
3	Engineering long spin coherence times of spinâ€“orbit qubits in silicon. Nature Materials, 2021, 20, 38-42.	27.5	40
4	Coherent control of a donor-molecule electron spin qubit in silicon. Nature Communications, 2021, 12, 3323.	12.8	27
5	Monolithic Three-Dimensional Tuning of an Atomically Defined Silicon Tunnel Junction. Nano Letters, 2021, 21, 10092-10098.	9.1	5
6	Exploiting a Singleâ€Crystal Environment to Minimize the Charge Noise on Qubits in Silicon. Advanced Materials, 2020, 32, e2003361.	21.0	41
7	A two-qubit gate between phosphorus donor electrons in silicon. Nature, 2019, 571, 371-375.	27.8	222
8	Benchmarking high fidelity single-shot readout of semiconductor qubits. New Journal of Physics, 2019, 21, 063011.	2.9	29
9	Spin read-out in atomic qubits in an all-epitaxial three-dimensional transistor. Nature Nanotechnology, 2019, 14, 137-140.	31.5	50
10	Two-electron spin correlations in precision placed donors in silicon. Nature Communications, 2018, 9, 980.	12.8	57
11	Two-electron states of a group-V donor in silicon from atomistic full configuration interactions. Physical Review B, 2018, 97, .	3.2	18
12	Single-Shot Single-Gate rf Spin Readout in Silicon. Physical Review X, 2018, 8, .	8.9	47
13	Readout and control of the spin-orbit states of two coupled acceptor atoms in a silicon transistor. Science Advances, 2018, 4, eaat9199.	10.3	26
14	Spinâ€“orbit coupling in silicon for electrons bound to donors. Npj Quantum Information, 2018, 4, .	6.7	17
15	Valley Filtering in Spatial Maps of Coupling between Silicon Donors and Quantum Dots. Physical Review X, 2018, 8, .	8.9	13
16	Characterization of a Scalable Donor-Based Singletâ€“Triplet Qubit Architecture in Silicon. Nano Letters, 2018, 18, 4081-4085.	9.1	10
17	Addressable electron spin resonance using donors and donor molecules in silicon. Science Advances, 2018, 4, eaaq1459.	10.3	36
18	Singlet-triplet minus mixing and relaxation lifetimes in a double donor dot. Applied Physics Letters, 2018, 112, 243105.	3.3	2

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19	<i>In Situ</i> Patterning of Ultrasharp Dopant Profiles in Silicon. ACS Nano, 2017, 11, 1683-1688.	14.6	7
20	Dephasing rates for weak localization and universal conductance fluctuations in two dimensional Si:P and Ge:P Î´-layers. Scientific Reports, 2017, 7, 46670.	3.3	9
21	Atomically engineered electron spin lifetimes of 30 s in silicon. Science Advances, 2017, 3, e1602811.	10.3	57
22	Tunneling Statistics for Analysis of Spin-Readout Fidelity. Physical Review Applied, 2017, 8, .	3.8	16
23	High-Fidelity Single-Shot Singlet-Triplet Readout of Precision-Placed Donors in Silicon. Physical Review Letters, 2017, 119, 046802.	7.8	34
24	Probing the Quantum States of a Single Atom Transistor at Microwave Frequencies. ACS Nano, 2017, 11, 2444-2451.	14.6	19
25	Electron spin relaxation of single phosphorus donors and donor clusters in atomically engineered silicon devices. , 2017, , .		0
26	Extracting inter-dot tunnel couplings between few donor quantum dots in silicon. New Journal of Physics, 2016, 18, 053041.	2.9	7
27	Reaction paths of phosphine dissociation on silicon (001). Journal of Chemical Physics, 2016, 144, 014705.	3.0	36
28	Quantum simulation of the Hubbard model with dopant atoms in silicon. Nature Communications, 2016, 7, 11342.	12.8	81
29	Atomic-precision architectures for the high-fidelity spin read-out of phosphorus donors in silicon. , 2016, , .		0
30	Determining the quantum-coherent to semiclassical transition in atomic-scale quasi-one-dimensional metals. Physical Review B, 2016, 94, .	3.2	2
31	Ultralow-Noise Atomic-Scale Structures for Quantum Circuitry in Silicon. Nano Letters, 2016, 16, 5779-5784.	9.1	20
32	Manifestation of a non-Abelian Berry phase in a<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>p</mml:mi></mml:math>-type semiconductor system. Physical Review B, 2016, 93, .	3.2	14
33	Publisher's Note: Manifestation of a non-Abelian Berry phase in ap-type semiconductor system [Phys. Rev. B93, 205424 (2016)]. Physical Review B, 2016, 93, .	3.2	0
34	Characterizing Si:P quantum dot qubits with spin resonance techniques. Scientific Reports, 2016, 6, 31830.	3.3	17
35	High-Sensitivity Charge Detection with a Single-Lead Quantum Dot for Scalable Quantum Computation. Physical Review Applied, 2016, 6, .	3.8	30
36	Mapping the chemical potential landscape of a triple quantum dot. Physical Review B, 2016, 94, .	3.2	4

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37	Highly tunable exchange in donor qubits in silicon. Npj Quantum Information, 2016, 2, .	6.7	45
38	Resonant tunneling spectroscopy of valley eigenstates on a donor-quantum dot coupled system. Applied Physics Letters, 2016, 108, 152102.	3.3	6
39	Spatial metrology of dopants in silicon with exact lattice site precision. Nature Nanotechnology, 2016, 11, 763-768.	31.5	45
40	Strain and electric field control of hyperfine interactions for donor spin qubits in silicon. Physical Review B, 2015, 91, .	3.2	17
41	Impact of nuclear spin dynamics on electron transport through donors. Physical Review B, 2015, 92, .	3.2	9
42	Quantum dot spectroscopy using a single phosphorus donor. Physical Review B, 2015, 92, .	3.2	10
43	High-Fidelity Rapid Initialization and Read-Out of an Electron Spin via the Single Donor<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msup><mml:mi>D</mml:mi><mml:mo>âˆ’</mml:mo></mml:msup></mml:math>Charge State. Physical Review Letters, 2015, 115, 166806.	7.8	48
44	Bottom-up assembly of metallic germanium. Scientific Reports, 2015, 5, 12948.	3.3	21
45	A new horizon for quantum information. Npj Quantum Information, 2015, 1, .	6.7	2
46	Charge sensing of a few-donor double quantum dot in silicon. Applied Physics Letters, 2015, 107, .	3.3	6
47	The Impact of Dopant Segregation on the Maximum Carrier Density in Si:P Multilayers. ACS Nano, 2015, 9, 7080-7084.	14.6	19
48	A surface code quantum computer in silicon. Science Advances, 2015, 1, e1500707.	10.3	193
49	Interface-induced heavy-hole/light-hole splitting of acceptors in silicon. Applied Physics Letters, 2015, 106, .	3.3	15
50	Radio frequency reflectometry and charge sensing of a precision placed donor in silicon. Applied Physics Letters, 2015, 107, .	3.3	22
51	Suppressing Segregation in Highly Phosphorus Doped Silicon Monolayers. ACS Nano, 2015, 9, 12537-12541.	14.6	36
52	Radio frequency measurements of tunnel couplings and singletâ€“triplet spin states in Si:P quantum dots. Nature Communications, 2015, 6, 8848.	12.8	49
53	A Tight-Binding Study of Single-Atom Transistors. Small, 2015, 11, 374-381.	10.0	14
54	Spin-Lattice Relaxation Times of Single Donors and Donor Clusters in Silicon. Physical Review Letters, 2014, 113, 246406.	7.8	27

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55	Limits to Metallic Conduction in Atomic-Scale Quasi-One-Dimensional Silicon Wires. Physical Review Letters, 2014, 113, 246802.	7.8	23
56	Silicon at the fundamental scaling limit-atomic-scale donor-based quantum electronics. , 2014, , .		0
57	Statistical modeling of ultra-scaled donor-based silicon phosphorus devices. , 2014, , .		0
58	Low resistivity, super-saturation phosphorus-in-silicon monolayer doping. Applied Physics Letters, 2014, 104, .	3.3	25
59	Single-charge detection by an atomic precision tunnel junction. Applied Physics Letters, 2014, 104, .	3.3	16
60	Noncollinear Paramagnetism of a GaAs Two-Dimensional Hole System. Physical Review Letters, 2014, 113, 236401.	7.8	9
61	Imaging of buried phosphorus nanostructures in silicon using scanning tunneling microscopy. Applied Physics Letters, 2014, 104, .	3.3	8
62	Disentangling phonon and impurity interactions in Î´-doped Si(001). Applied Physics Letters, 2014, 104, 173108.	3.3	16
63	Lithography and doping in strained Si towards atomically precise device fabrication. Nanotechnology, 2014, 25, 145302.	2.6	12
64	Spatially resolving valley quantum interference of a donor in silicon. Nature Materials, 2014, 13, 605-610.	27.5	90
65	Determining the Electronic Confinement of a Subsurface Metallic State. ACS Nano, 2014, 8, 10223-10228.	14.6	11
66	Transport in Asymmetrically Coupled Donor-Based Silicon Triple Quantum Dots. Nano Letters, 2014, 14, 1830-1835.	9.1	23
67	Determination of the free carrier concentration in atomic-layer doped germanium thin films by infrared spectroscopy. Journal of Optics (United Kingdom), 2014, 16, 094010.	2.2	8
68	Valley Splitting in a Silicon Quantum Device Platform. Nano Letters, 2014, 14, 1515-1519.	9.1	18
69	Spin blockade and exchange in Coulomb-confined silicon double quantum dots. Nature Nanotechnology, 2014, 9, 430-435.	31.5	117
70	Spontaneous Breaking of Time-Reversal Symmetry in Strongly Interacting Two-Dimensional Electron Layers in Silicon and Germanium. Physical Review Letters, 2014, 112, 236602.	7.8	17
71	Silicon quantum electronics. Reviews of Modern Physics, 2013, 85, 961-1019.	45.6	892
72	New avenues to an old material: controlled nanoscale doping of germanium. Nanoscale, 2013, 5, 2600.	5.6	43

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73	Direct measurement of the spin gaps in a gated GaAs two-dimensional electron gas. Nanoscale Research Letters, 2013, 8, 138.	5.7	3
74	Transport through a single donor in p-type silicon. Applied Physics Letters, 2013, 103, 043106.	3.3	17
75	A tight-binding study of channel modulation in atomic-scale Si:P nanowires. , 2013, , .		0
76	Atomistic modeling of metallic nanowires in silicon. Nanoscale, 2013, 5, 8666.	5.6	28
77	Thermal processing of strained silicon-on-insulator for atomically precise silicon device fabrication. Applied Surface Science, 2013, 265, 833-838.	6.1	3
78	Epitaxial top-gated atomic-scale silicon wire in a three-dimensional architecture. Nanotechnology, 2013, 24, 045303.	2.6	28
79	Direct Measurement of the Band Structure of a Buried Two-Dimensional Electron Gas. Physical Review Letters, 2013, 110, 136801.	7.8	30
80	Exploring the Limits of N-Type Ultra-Shallow Junction Formation. ACS Nano, 2013, 7, 5499-5505.	14.6	44
81	Spin readout and addressability of phosphorus-donor clusters in silicon. Nature Communications, 2013, 4, 2017.	12.8	100
82	Phosphorus Molecules on Ge(001): A Playground for Controlled n-Doping of Germanium at High Densities. ACS Nano, 2013, 7, 11310-11316.	14.6	24
83	Electronic spectrum of a deterministic single-donor device in silicon. , 2013, , .		0
84	Origin of noise in two dimensionally doped silicon and germanium. , 2013, , .		0
85	Electronic structure of phosphorus and arsenicÎ´-doped germanium. Physical Review B, 2013, 88, .	3.2	4
86	Interplay between quantum confinement and dielectric mismatch for ultrashallow dopants. Physical Review B, 2013, 87, .	3.2	18
87	Atomic layer doping of strained Ge-on-insulator thin films with high electron densities. Applied Physics Letters, 2013, 102, 151103.	3.3	16
88	Using Scanning Tunneling Microscopy to Realize Atomic- Scale Silicon Devices. , 2013, , .		1
89	Microscopic four-point-probe resistivity measurements of shallow, high density doping layers in silicon. Applied Physics Letters, 2012, 101, .	3.3	32
90	Full-band study of ultra-thin Si:P nanowires. , 2012, , .		0

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91	<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>n</mml:mi></mml:math>-Type Doping of Germanium from Phosphine: Early Stages Resolved at the Atomic Level. Physical Review Letters, 2012, 109, 076101.	7.8	18
92	Effective mass theory of monolayer<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>Î´</mml:mi></mml:math>doping in the high-density limit. Physical Review B, 2012, 85, .	3.2	24
93	Stacking of 2D Electron Gases in Ge Probed at the Atomic Level and Its Correlation to Low-Temperature Magnetotransport. Nano Letters, 2012, 12, 4953-4959.	9.1	17
94	Spectroscopy of a deterministic single-donor device in silicon. Proceedings of SPIE, 2012, , .	0.8	3
95	Engineering Independent Electrostatic Control of Atomic-Scale (â^¼4 nm) Silicon Double Quantum Dots. Nano Letters, 2012, 12, 4001-4006.	9.1	31
96	Ohmâ€™s Law Survives to the Atomic Scale. Science, 2012, 335, 64-67.	12.6	291
97	A single-atom transistor. Nature Nanotechnology, 2012, 7, 242-246.	31.5	730
98	A Complete Fabrication Route for Atomic-Scale, Donor-Based Devices in Single-Crystal Germanium. Nano Letters, 2011, 11, 2272-2279.	9.1	60
99	Charge Sensing of Precisely Positioned P Donors in Si. Nano Letters, 2011, 11, 4376-4381.	9.1	43
100	Comparison of nickel silicide and aluminium ohmic contact metallizations for low-temperature quantum transport measurements. Nanoscale Research Letters, 2011, 6, 538.	5.7	9
101	Dual-temperature encapsulation of phosphorus in germanium Î´â€layers toward ultra-shallow junctions. Journal of Crystal Growth, 2011, 316, 81-84.	1.5	10
102	Phosphorus atomic layer doping of germanium by the stacking of multiple Î´ layers. Nanotechnology, 2011, 22, 375203.	2.6	26
103	Suppression of low-frequency noise in two-dimensional electron gas at degenerately doped Si:P<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi>Î´</mml:mi></mml:mrow></mml:math>layers. Physical Review B, 2011, 83, .	3.2	16
104	Electronic structure of realistically extended atomistically resolved disordered Si:P<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>Î´</mml:mi></mml:math>-doped layers. Physical Review B, 2011, 84, .	3.2	44
105	First-principles modelling of scanning tunneling microscopy using non-equilibrium Greenâ€™s functions. Frontiers of Physics in China, 2010, 5, 369-379.	1.0	13
106	Optimizing dopant activation in Si:P double <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si0014.gif" overflow="scroll"><mml:mi mathvariant="normal">Î´</mml:mi><mml:mtext>-layers</mml:mtext></mml:math>. Journal of Crystal Growth, 2010, 312, 3247-3250.	1.5	14
107	Investigating the surface quality and confinement of Si:P at different growth temperatures. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 1180-1183.	2.7	15
108	Radio-frequency reflectometryâ€"A fast and sensitive measurement method for two-dimensional systems. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 1192-1195.	2.7	1

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109	Spectroscopy of few-electron single-crystal silicon quantum dots. Nature Nanotechnology, 2010, 5, 502-505.	31.5	165
110	Development of a tunable donor quantum dot in silicon. Applied Physics Letters, 2010, 96, 043116.	3.3	13
111	Influence of encapsulation temperature on Ge:PÎ´-doped layers. Physical Review B, 2009, 80, .	3.2	23
112	Ultradense phosphorus in germanium delta-doped layers. Applied Physics Letters, 2009, 94, 162106.	3.3	45
113	Investigating the regrowth surface of Si:P Î´-layers toward vertically stacked three dimensional devices. Applied Physics Letters, 2009, 95, .	3.3	39
114	Atomic-scale patterning of hydrogen terminated Ge(001) by scanning tunneling microscopy. Nanotechnology, 2009, 20, 495302.	2.6	28
115	Aharonovâ€“Bohm oscillations in a nanoscale dopant ring in silicon. Applied Physics Letters, 2009, 95, .	3.3	3
116	Impact of Si growth rate on coherent electron transport in Si:P delta-doped devices. Applied Physics Letters, 2009, 95, 142104.	3.3	11
117	Atomic-Scale, All Epitaxial In-Plane Gated Donor Quantum Dot in Silicon. Nano Letters, 2009, 9, 707-710.	9.1	104
118	NANOTECHNOLOGY IN AUSTRALIA. , 2009, , 37-57.		0
119	Demonstration of gating action in atomically controlled Si:P nanodots defined by scanning probe microscopy. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 1006-1009.	2.7	5
120	0.7 Structure and zero bias anomaly in one-dimensional hole systems. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 1501-1503.	2.7	0
121	Metallic behavior in low-disorder two-dimensional hole systems in the presence of long- and short-range disorder. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 1599-1601.	2.7	0
122	The effect of surface proximity on electron transport through ultra-shallow -doped layers in silicon. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 1566-1568.	2.7	11
123	Using a four-probe scanning tunneling microscope to characterize phosphorus doped ohmic contacts for atomic scale devices in silicon. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 2131-2133.	2.7	1
124	Geometric suppression of single-particle energy spacings in quantum antidots. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 1633-1636.	2.7	1
125	Screening long-range Coulomb interactions in 2D hole systems using a bilayer heterostructure. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 1700-1702.	2.7	1
126	Impact of long- and short-range disorder on the metallic behaviour of two-dimensional systems. Nature Physics, 2008, 4, 55-59.	16.7	39

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127	Probing dopants at the atomic level. Nature Physics, 2008, 4, 165-166.	16.7	9
128	The 0.7 anomaly in one-dimensional hole quantum wires. Journal of Physics Condensed Matter, 2008, 20, 164205.	1.8	10
129	Enhancing electron transport in Si:P delta-doped devices by rapid thermal anneal. Applied Physics Letters, 2008, 93, 142105.	3.3	13
130	Effect of screening long-range Coulomb interactions on the metallic behavior in two-dimensional hole systems. Physical Review B, 2008, 77, .	3.2	14
131	Electron-electron interactions in highly disordered two-dimensional systems. Physical Review B, 2008, 77, .	3.2	40
132	Radio-frequency reflectometry on large gated two-dimensional systems. Review of Scientific Instruments, 2008, 79, 123901.	1.3	12
133	Ohmic conduction of sub-10nm P-doped silicon nanowires at cryogenic temperatures. Applied Physics Letters, 2008, 92, 052101.	3.3	12
134	Electron heating and huge positive magnetoresistance in an AlGaAsâˆ•GaAs high electron mobility transistor structure at high temperatures. Applied Physics Letters, 2008, 92, 152117.	3.3	6
135	0.7 Structure and Zero Bias Anomaly in Ballistic Hole Quantum Wires. Physical Review Letters, 2008, 100, 016403.	7.8	27
136	Anticrossing of Spin-Split Subbands in Quasi-One-Dimensional Wires. Physical Review Letters, 2008, 100, 226804.	7.8	2
137	Kondo Effect from a Tunable Bound State within a Quantum Wire. Physical Review Letters, 2008, 100, 026807.	7.8	57
138	Quantum transport in one-dimensional GaAs hole systems. International Journal of Nanotechnology, 2008, 5, 318.	0.2	1
139	Morphology and electrical conduction of Si:P Î´-doped layers on vicinal Si(001). Journal of Applied Physics, 2008, 104, 066104.	2.5	10
140	Surface gate and contact alignment for buried, atomically precise scanning tunneling microscopyâ€"patterned devices. Journal of Vacuum Science & Technology B, 2007, 25, 2562.	1.3	20
141	Decay of long-lived quantum Hall induced currents in 2D electron systems. New Journal of Physics, 2007, 9, 71-71.	2.9	8
142	Comparison of GaP and PH3 as dopant sources for STM-based device fabrication. Nanotechnology, 2007, 18, 065301.	2.6	8
143	Scanning tunneling microscope based fabrication of nano- and atomic scale dopant devices in silicon: The crucial step of hydrogen removal. Journal of Applied Physics, 2007, 101, 034305.	2.5	26
144	Atomically precise silicon device fabrication. , 2007, , .		1

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145	Single hydrogen atoms on the Si(001) surface. Physical Review B, 2007, 76, .	3.2	28
146	Energy-level pinning and the 0.7 spin state in one dimension: GaAs quantum wires studied using finite-bias spectroscopy. Physical Review B, 2007, 75, .	3.2	32
147	Huge positive magnetoresistance of GaAsâˆ•AlGaAs high electron mobility transistor structures at high temperatures. Applied Physics Letters, 2007, 90, 252106.	3.3	12
148	Structural and electrical characterization of room temperature ultra-high-vacuum compatible SiO2 for gating scanning tunneling microscope-patterned devices. Applied Physics Letters, 2007, 91, 222109.	3.3	6
149	Use of a scanning electron microscope to pattern large areas of a hydrogen resist for electrical contacts. Journal of Applied Physics, 2007, 102, .	2.5	8
150	Use of low-temperature Hall effect to measure dopant activation: Role of electron-electron interactions. Physical Review B, 2007, 76, .	3.2	6
151	Electronic properties of atomically abrupt tunnel junctions in silicon. Physical Review B, 2007, 75, .	3.2	31
152	One-dimensional conduction properties of highly phosphorus-doped planar nanowires patterned by scanning probe microscopy. Physical Review B, 2007, 76, .	3.2	33
153	Single P and As dopants in the Si(001) surface. Journal of Chemical Physics, 2007, 127, 184706.	3.0	8
154	Narrow, highly P-doped, planar wires in silicon created by scanning probe microscopy. Nanotechnology, 2007, 18, 044023.	2.6	24
155	Electrical Characterization of Ordered Si:P Dopant Arrays. IEEE Nanotechnology Magazine, 2007, 6, 213-217.	2.0	17
156	Single Phosphorus Atoms in Si(001):â€‰ Doping-Induced Charge Transfer into Isolated Si Dangling Bonds. Journal of Physical Chemistry C, 2007, 111, 6428-6433.	3.1	5
157	Doping and STM tip-induced changes to single dangling bonds on Si(001). Surface Science, 2007, 601, 4036-4040.	1.9	10
158	Realization of Atomically Controlled Dopant Devices in Silicon. Small, 2007, 3, 563-567.	10.0	108
159	Thermal dissociation and desorption ofPH3on Si(001): A reinterpretation of spectroscopic data. Physical Review B, 2006, 74, .	3.2	57
160	Phosphine Dissociation and Diffusion on Si(001) Observed at the Atomic Scale. Journal of Physical Chemistry B, 2006, 110, 3173-3179.	2.6	28
161	BASIC PROPERTIES OF SILICON SURFACES. , 2006, , 29-66.		0
162	The excitation spectrum of quantum antidots. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 34, 195-198.	2.7	7

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163	Ballistic transport in one-dimensional bilayer hole systems. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 34, 550-552.	2.7	2
164	Effects of interactions and disorder on the compressibility of two-dimensional electron and hole systems. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 34, 240-243.	2.7	2
165	New interaction effects in quantum point contacts at high magnetic fields. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 34, 588-591.	2.7	6
166	Phosphorus and hydrogen atoms on the (001) surface of silicon: A comparative scanning tunnelling microscopy study of surface species with a single dangling bond. Surface Science, 2006, 600, 318-324.	1.9	20
167	Zeeman Splitting in Ballistic Hole Quantum Wires. Physical Review Letters, 2006, 97, 026403.	7.8	85
168	Fabrication of induced two-dimensional hole systems on (311)A GaAs. Journal of Applied Physics, 2006, 99, 023707.	2.5	30
169	Conductance quantization and the 0.7Ã—2e2âˆ•h conductance anomaly in one-dimensional hole systems. Applied Physics Letters, 2006, 88, 012107.	3.3	42
170	Thermodynamic Density of States of Two-Dimensional GaAs Systems near the Apparent Metal-Insulator Transition. Physical Review Letters, 2006, 96, 216407.	7.8	50
171	Influence of doping density on electronic transport in degenerate Si:PÎ´-doped layers. Physical Review B, 2006, 73, .	3.2	62
172	Importance of charging in atomic resolution scanning tunneling microscopy: Study of a single phosphorus atom in aSi(001)surface. Physical Review B, 2006, 74, .	3.2	14
173	The fabrication of devices in silicon using scanning probe microscopy. , 2005, , .		0
174	STM characterization of phosphine adsorption on STM-patterned H:Si(001)surfaces. , 2005, , .		1
175	Fabrication and characterization of a 2D hole system a in novel (311)A GaAs SISFET. Microelectronics Journal, 2005, 36, 327-330.	2.0	2
176	Evidence for a finite compressibility of a quasi-one-dimensional ballistic channel. Microelectronics Journal, 2005, 36, 331-333.	2.0	0
177	â€˜Mobility gapâ€™ of a spin-split GaAs two-dimensional electron gas. Microelectronics Journal, 2005, 36, 466-468.	2.0	1
178	Induced currents, frozen charges and the quantum Hall effect breakdown. Solid State Communications, 2005, 134, 257-259.	1.9	5
179	Relevance of phosphorus incorporation and hydrogen removal for Si:P Î´-doped layers fabricated using phosphine. Physica Status Solidi (A) Applications and Materials Science, 2005, 202, 1002-1005.	1.8	10
180	Interaction effects in high-mobility two-dimensional electron and hole systems. Physica Status Solidi (B): Basic Research, 2005, 242, 1204-1208.	1.5	1

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181	Towards the Routine Fabrication of P in Si Nanostructures: Understanding P Precursor Molecules on Si(001). Materials Research Society Symposia Proceedings, 2005, 864, 541.	0.1	2
182	The use of etched registration markers to make four-terminal electrical contacts to STM-patterned nanostructures. Nanotechnology, 2005, 16, 2446-2449.	2.6	26
183	Interaction correction to the longitudinal conductivity and Hall resistivity in high-quality two-dimensional GaAs electron and hole systems. Physical Review B, 2005, 72, .	3.2	10
184	Phosphine adsorption and dissociation on the Si(001) surface: Anab initiosurvey of structures. Physical Review B, 2005, 72, .	3.2	44
185	Observation of substitutional and interstitial phosphorus on cleanSi(100)â^'(2Ã—1)with scanning tunneling microscopy. Physical Review B, 2005, 72, .	3.2	11
186	Evolution of the bilayerÎ½=1quantum Hall state under charge imbalance. Physical Review B, 2005, 71, .	3.2	15
187	Effective removal of hydrogen resists used to pattern devices in silicon using scanning tunneling microscopy. Applied Physics Letters, 2005, 86, 143116.	3.3	11
188	Anomalous spin-dependent behavior of one-dimensional subbands. Physical Review B, 2005, 72, .	3.2	15
189	Scanning probe microscopy for silicon device fabrication. Molecular Simulation, 2005, 31, 505-515.	2.0	50
190	Measurements of composite fermion conductivity dependence on carrier density. Journal of Physics Condensed Matter, 2004, 16, 1095-1101.	1.8	1
191	Unusual conductance collapse in one-dimensional quantum structures. Journal of Physics Condensed Matter, 2004, 16, L279-L286.	1.8	8
192	Measurement of phosphorus segregation in silicon at the atomic scale using scanning tunneling microscopy. Applied Physics Letters, 2004, 85, 1359-1361.	3.3	49
193	Temperature dependence of the breakdown of the quantum Hall effect studied by induced currents. Physical Review B, 2004, 70, .	3.2	33
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